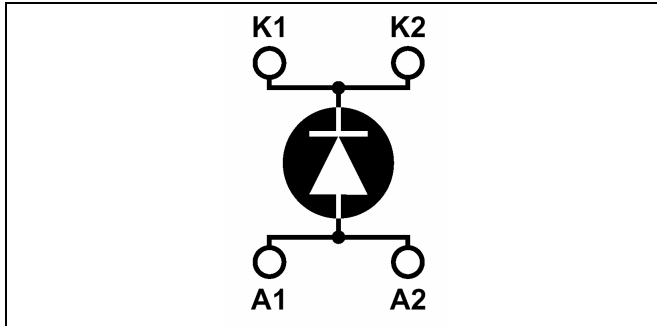


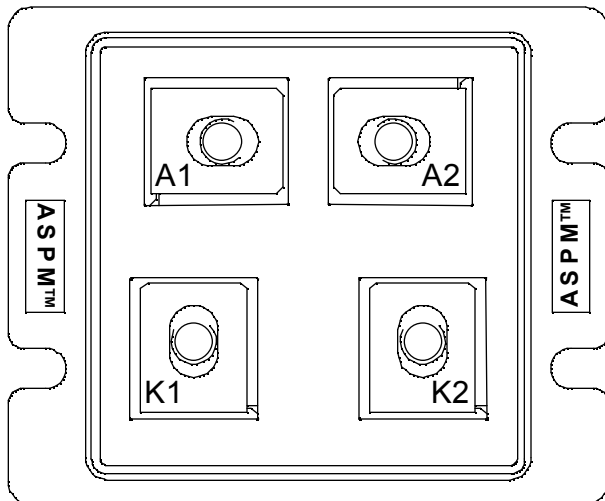
Single diode Power Module

$V_{CES} = 200V$
 $I_C = 500A @ T_c = 80^\circ C$



Application

- Anti-Parallel diode
 - Switchmode Power Supply
 - Inverters
- Snubber diode
- Uninterruptible Power Supply (UPS)
- Induction heating
- Welding equipment
- High speed rectifiers
- Electric vehicles



Features

- Ultra fast recovery times
- Soft recovery characteristics
- Very low stray inductance
- High blocking voltage
- High current
- Low leakage current

Benefits

- Low losses
- Low noise switching
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit	
V_R	Maximum DC reverse Voltage	200	V	
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			
$I_{F(AV)}$	Maximum Average Forward Current	Duty cycle = 50%	$T_c = 25^\circ C$	A
			$T_c = 80^\circ C$	
$I_{F(RMS)}$	RMS Forward Current	850		
I_{FSM}	Non-Repetitive Forward Surge Current	$T_j = 25^\circ C$	5000	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

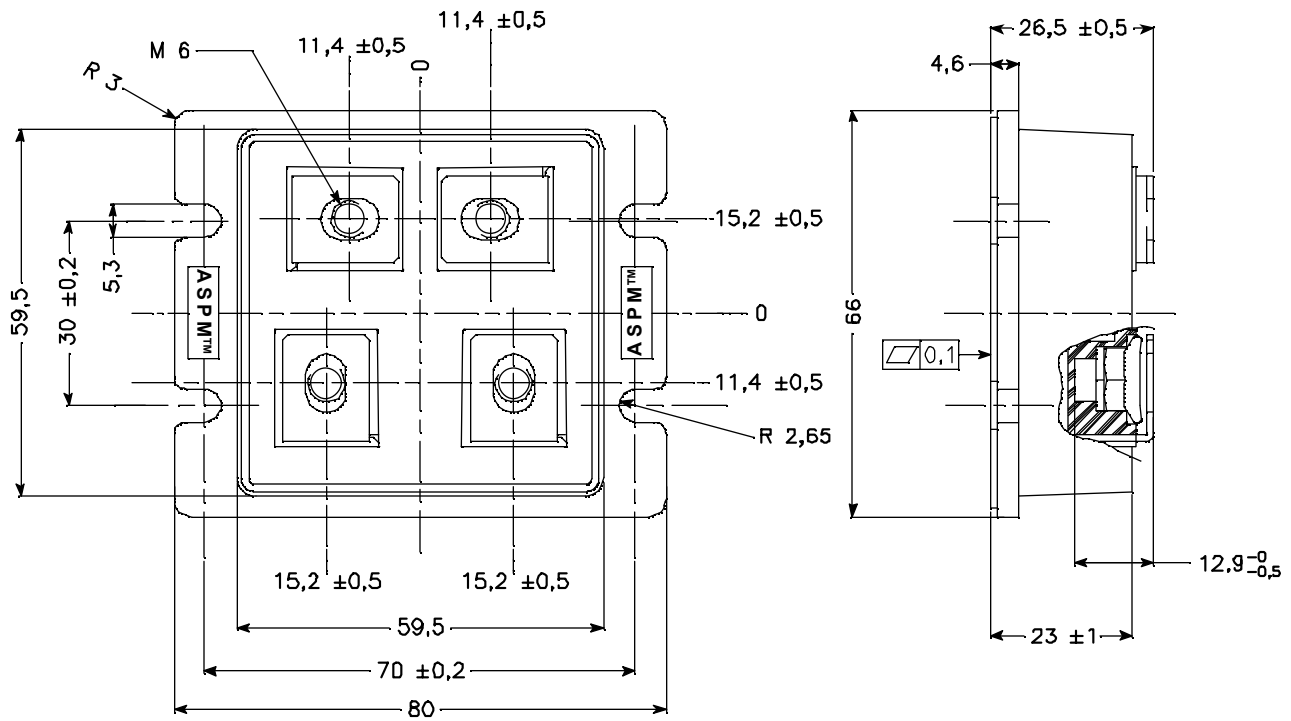
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Diode Forward Voltage	$I_F = 500\text{A}$			1.1	V
		$I_F = 1000\text{A}$		1.25		
		$I_F = 500\text{A}$	$T_j = 150^\circ\text{C}$		0.95	
I_{RM}	Maximum Reverse Leakage Current	$V_R = 200\text{V}$	$T_j = 25^\circ\text{C}$		2500	μA
			$T_j = 150^\circ\text{C}$		5000	
C_T	Junction Capacitance	$V_R = 200\text{V}$		1000		pF
L_S	Series Inductance	Lead to Lead 5mm from Base		30	40	nH

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
t_{rr1}	Reverse Recovery Time	$I_F = 1\text{A}, V_R = 30\text{V}$ $di/dt = 15\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		70	ns
t_{rr2}			$T_j = 25^\circ\text{C}$		70	
t_{rr3}			$T_j = 100^\circ\text{C}$		150	
t_{fr1}	Forward Recovery Time	$I_F = 500\text{A}$ $V_R = 100\text{V}$ $di/dt = 800\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		250	ns
t_{fr2}			$T_j = 100^\circ\text{C}$		250	
I_{RRM1}	Reverse Recovery Current		$T_j = 25^\circ\text{C}$		50	A
I_{RRM2}			$T_j = 100^\circ\text{C}$		120	
Q_{rr1}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		4.9	μC
Q_{rr2}			$T_j = 100^\circ\text{C}$		22	
V_{fr1}	Forward Recovery Voltage		$T_j = 25^\circ\text{C}$		15	V
V_{fr2}			$T_j = 100^\circ\text{C}$		15	
d_{IM}/dt	Rate of Fall of Recovery Current		$T_j = 25^\circ\text{C}$		1200	$\text{A}/\mu\text{s}$
			$T_j = 100^\circ\text{C}$		1800	

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R_{thJC}	Junction to Case Thermal Resistance			0.08	$^\circ\text{C}/\text{W}$	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1\text{ min}, I_{isol} < 1\text{mA}, 50/60\text{Hz}$	2500			V	
T_J	Operating junction temperature range	-40		150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-40		125		
T_C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M5	2.5	3.5	N.m
		For terminals	M6	3	4	
Wt	Package Weight			250	g	

LP4 Package outline (dimensions in mm)


Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.